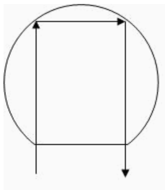
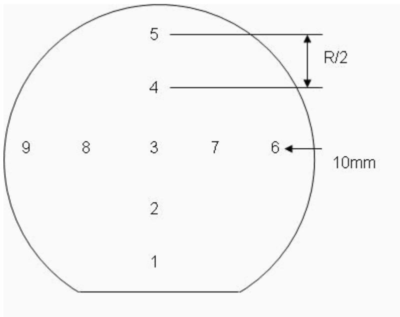
Part Number Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	<110> +/- 0.5 degree	Wafer Vendor
	4.0	Secondary Flat Length	None	Wafer Vendor
	5.0	Overall Thickness	420.50 +/- 7.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	none	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
	11.0	Wafer Oxygen concentration	<20 ppm	Wafer Vendor
HandleSilicon	12.0	Handle Growth Method	CZ or MCZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	380.00 +/- 5.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorus	Wafer Vendor
	17.0	Handle Resistivity	1 ~ 10 Ohm cm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide, laser mark, and light handling marks	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	5,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	40.00 +/- 2.00 µm	Filmetrics 9 point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	25.0	Edge Removal Depth in Handle	<100um	Guaranteed by process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorus	Wafer Vendor
	28.0	Device Growth Method	CZ or MCZ	Wafer Vendor
	29.0	Device Resistivity	1 ~ 5 Ohm cm	Wafer Vendor
	30.0	Voids	none	Bright Light, 100% (note 2)
	31.0	Scratches	none	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)
	33.0	Laser marking	Device Frondside, Include: DEV40	Graranteed by process

Part Number Customer

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below: 		
Additional Information			